

METHOD FOR THE DEPOSITION OF A REACTION CHAMBER FOR THE DEPOSITION OF SILICON NITRIDE FILMS

Abstract of the Disclosure

A method is provided for obtaining stable and elevated deposition rates in a reaction chamber, following the cleaning of the chamber. The method involves cleaning of the chamber, pre-coating the interior surfaces of the reaction chamber with an inorganic composition, and then, using the pre-coated chamber to deposit an organic layer onto a workpiece.

W:\DOCS\EAL\EAL-1084.DOC
101503